

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L14	12	((diode or semiconductor) near2 laser) and (conduct\$3 near2 (layer or film or region medium)) and (metal\$3 near2 (block or layer or film or region or medium)) and ((thermal\$3 or heat) near2 sink) and electrode and (capacitor with parallel)	US-PGPUB; USPAT	AND	ON	2006/01/31 10:28
L16	6	((diode or semiconductor) near2 laser) and (conduct\$3 near2 (layer or film or region medium)) and (metal\$3 near2 (block or layer or film or region or medium)) and ((thermal\$3 or heat) near2 sink) and electrode and (capacitor near3 plate)	US-PGPUB; USPAT	AND	ON	2006/01/31 10:25
L15	8	((diode or semiconductor) near2 laser) and (conduct\$3 near2 (layer or film or region medium)) and (metal\$3 near2 (block or layer or film or region or medium)) and ((thermal\$3 or heat) near2 sink) and electrode and (capacitor with plate)	US-PGPUB; USPAT	AND	ON	2006/01/31 10:25
L11	109	((diode or semiconductor) near2 laser) and (conduct\$3 near2 (layer or film or region medium)) and (metal\$3 near2 (block or layer or film or region or medium)) and ((thermal\$3 or heat) near2 sink) and electrode and capacitor	US-PGPUB; USPAT	AND	ON	2006/01/31 10:09
L13	256	12 not 11	US-PGPUB; USPAT	AND	ON	2006/01/31 09:58
L12	365	((diode or semiconductor) near2 laser) and (conduct\$3 near2 (layer or film or region medium)) and (metal\$3 near2 (block or layer or film or region or medium)) and ((thermal\$3 or heat) near2 sink) and electrode	US-PGPUB; USPAT	AND	ON	2006/01/31 09:58
L10	223	((diode or semiconductor) near2 laser) and (conduct\$3 near2 (layer or film or region medium)) and (metal\$3 near2 (block or layer or film or region or medium)) and ((thermal\$3 or heat) near2 sink) and electrode and capacit\$3	US-PGPUB; USPAT	AND	ON	2006/01/31 09:58
L6	516	laser and (conduct\$3 near2 (layer or film or region medium)) and (metal\$3 near2 (block or layer or film or region or medium)) and ((thermal\$3 or heat) near2 sink) and electrode and capacit\$3	US-PGPUB; USPAT	AND	ON	2006/01/31 09:48
L9	14	("3875532" "5068865" "5247530" "5420722" "5706302" "5757830" "5793792" "5974065" "5995525" "6101202" "6625185" "6676306" "6721341" "6810049").PN. OR ("6985506").URPN.	US-PGPUB; USPAT; USOCR	AND	ON	2006/01/31 09:21
L8	98	((("4818099") or ("5923692") or ("4348253") or ("4628695") or ("5388755") or ("5812570") or ("5832016") or ("5835345") or ("5848083") or ("5898211") or ("5903583") or ("5985684") or ("6007730") or ("6088256") or ("6266353") or ("6535533") or ("6870866") or ("5757027") or ("5891746") or ("6013537") or ("6273400") or ("5309269") or ("5181214") or ("4538169") or ("4589116") or ("4592059") or ("4949346") or ("5008737") or ("5325384") or ("5608749") or ("6178189") or ("3896473") or ("4142893") or ("4161701") or ("4413343") or ("4454602") or ("4589586") or ("4623086") or ("4627062") or ("4811079") or ("4817854") or ("4854659") or ("4901324") or ("4947238") or ("4969155") or ("5038356") or ("5233622") or ("5238531") or ("5253263") or ("5259049").pn.) or ("5294381") or ("5311536") or ("5394426") or ("5453641") or ("5465171") or ("5495126") or ("5520244") or ("5522225") or ("5610930") or ("5636234") or ("5640407") or ("5665982") or ("5674779") or ("5745514") or ("5751013") or ("5781573") or ("5845031") or ("5872881") or ("5895225") or ("5909036") or ("5913108") or ("5924290") or ("5935294") or ("5943553") or ("5987043") or ("6028878") or ("6055815") or ("6072815") or ("6075800") or ("6133058") or ("6131650") or ("6136626") or ("6208677") or ("6240113") or ("6323530") or ("6345138") or ("6358316") or ("6370173") or ("6378321") or ("6459709") or ("6480514") or ("6480515") or ("6600763") or ("6608283") or ("6724791") or ("6965552") or ("6967980") or ("6985506") or ("5479029") or ("5471087").pn.)).PN.	US-PGPUB; USPAT	OR	OFF	2006/01/31 08:57
L7	2	laser and (conduct\$3 near2 (layer or film or region medium)) and (metal\$3 near2 (block or layer or film or region or medium)) and ((thermal\$3 or heat) near2 sink) and electrode and capacit\$3	USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/31 08:43
L5	852	laser and (conduct\$3 near2 (layer or film or region medium)) and (metal\$3 near2 (block or layer or film or region or medium)) and ((thermal\$3 or heat) near2 sink) and electrode	US-PGPUB; USPAT	AND	ON	2006/01/31 08:42

L3	1779	laser and (conduct\$3 near2 (layer or film or region medium)) and (metal\$3 near2 (block or layer or film or region or medium)) and ((thermal\$3 or heat) near3 sink)	US-PGPUB; USPAT	AND	ON	2006/01/31 08:30
L2	1406	laser and (conductive near2 (layer or film or region medium)) and (metal\$3 near2 (block or layer or film or region or medium)) and ((thermal\$3 or heat) near3 sink)	US-PGPUB; USPAT	AND	ON	2006/01/31 08:30
S76	30	laser and (parallel near2 plate near3 capacit\$3) and ((thermal\$3 or heat) near3 sink)	US-PGPUB; USPAT	AND	ON	2006/01/31 08:23
S32	116	((laser) and (heatsink or (heat near2 sink)) and ((conductive or dielectric) near2 (layer or film or medium or region)) and (metal\$3 near1 (layer or film or medium or region or block or base or mount)) and anode and cathode	USPAT	AND	ON	2006/01/30 17:28
S75	244	(parallel NEAR5 capacitor) and laser and ((thermal\$3 or heat) near3 sink)	US-PGPUB; USPAT	AND	ON	2006/01/30 17:27
S74	277	(parallel with capacitor) and laser and ((thermal\$3 or heat) near3 sink)	US-PGPUB; USPAT	AND	ON	2006/01/30 17:27
S64	70420	parallel with capacitor	US-PGPUB; USPAT	AND	ON	2006/01/30 14:08
S73	33	S70 and ((heat or thermal) with sink)	US-PGPUB; USPAT	AND	ON	2006/01/30 14:00
S72	28	S71 and ((heat or thermal) with sink)	US-PGPUB; USPAT	AND	ON	2006/01/30 14:00
S71	552	S70 and semiconductor	US-PGPUB; USPAT	AND	ON	2006/01/30 13:57
S70	958	S69 and laser	US-PGPUB; USPAT	AND	ON	2006/01/30 13:56
S69	5512	parallel with plate with capacitor	US-PGPUB; USPAT	AND	ON	2006/01/30 13:56
S68	30	S67 and ((heat or thermal) with sink)	US-PGPUB; USPAT	AND	ON	2006/01/30 13:55
S67	761	S66 and "257".clas.	US-PGPUB; USPAT	AND	ON	2006/01/30 13:54
S66	3187	S65 and semiconductor	US-PGPUB; USPAT	AND	ON	2006/01/30 13:54
S65	5883	S64 and laser	US-PGPUB; USPAT	AND	ON	2006/01/30 13:54
S62	264	(remmon near2 forde).xa.	US-PGPUB; USPAT	AND	ON	2006/01/30 13:29
S63	1	(remmon near2 forde).xa. and ((parallel near2 plate near2 capacitor) or (parallel-plate-capacitor))	US-PGPUB; USPAT	AND	ON	2006/01/30 13:28
S60	280	capacitor and (heatsink or (heat near1 sink) or heatsink) and ((conductive or insulator) near3 (layer or medium or region or film)) and (metal\$3 near1 (block or layer or region or film or medium)) and laser and ("372"/\$.ccls. or "257"/\$.ccls.)	US-PGPUB; USPAT	AND	ON	2006/01/30 13:27
S61	1	capacitor and (heatsink or (heat near1 sink) or heatsink) and ((conductive or insulator) near3 (layer or medium or region or film)) and (metal\$3 near1 (block or layer or region or film or medium)) and laser and ("372"/\$.ccls. or "257"/\$.ccls.)	USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/30 13:24
S59	329	capacitor and (heatsink or (heat near1 sink) or heatsink) and ((conductive or insulator) near3 (layer or medium or region or film)) and (metal\$3 near3 (block or layer or region or film or medium)) and laser and ("372"/\$.ccls. or "257"/\$.ccls.)	US-PGPUB; USPAT	AND	ON	2006/01/30 13:23
S58	329	capacitor and (heatsink or (heat near1 sink)) and ((conductive or insulator) near3 (layer or medium or region or film)) and (metal\$3 near3 (block or layer or region or film or medium)) and laser and ("372"/\$.ccls. or "257"/\$.ccls.)	US-PGPUB; USPAT	AND	ON	2006/01/30 12:54
S54	552	capacitor and (heatsink or (heat near1 sink)) and ((conductive or insulator) near3 (layer or medium or region or film)) and (metal\$3 near3 (block or layer or region or film or medium)) and laser	US-PGPUB; USPAT	AND	ON	2006/01/30 12:26
S56	10	S55 not S53	US-PGPUB; USPAT	AND	ON	2006/01/30 12:23

S55	22	capacitor and (heatsink or (heat near1 sink)) and ((conductive or insulator) near3 (layer or medium or region or film)) and (metal\$3 near3 (block or layer or region or film or medium)) and laser and (parallel near2 plate)	US-PGPUB; USPAT	AND	ON	2006/01/30 12:23
S53	12	((parallel near2 plate near2 capacitor) or (parallel-plate-capacitor)) and (heatsink or (heat near1 sink)) and ((conductive or insulator) near3 (layer or medium or region or film)) and (metal\$3 near3 (block or layer or region or film or medium)) and laser	US-PGPUB; USPAT	AND	ON	2006/01/30 12:10
S52	34	((parallel near2 plate near2 capacitor) or (parallel-plate-capacitor)) and (heatsink or (heat near1 sink)) and ((conductive or insulator) near3 (layer or medium or region or film)) and (metal\$3 near3 (block or layer or region or film or medium))	US-PGPUB; USPAT	AND	ON	2006/01/30 12:08
S48	39	((parallel near2 plate near2 capacitor) or (parallel-plate-capacitor)) and (heatsink or (heat near1 sink)) and (conductive) and (metal\$3 near3 (block or layer or region or film or medium))	US-PGPUB; USPAT	AND	ON	2006/01/30 12:07
S51	13	((parallel near2 plate near2 capacitor) or (parallel-plate-capacitor)) and (heatsink or (heat near1 sink)) and (conductive) and (metal\$3 near3 (block or layer or region or film or medium)) and laser	US-PGPUB; USPAT	AND	ON	2006/01/30 11:59
S50	0	((parallel near2 plate near2 capacitor) or (parallel-plate-capacitor)) and (heatsink or (heat near1 sink)) and (conductive) and (metal\$3 near3 (block or layer or region or film or medium)) and laser	USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/30 11:59
S49	0	((parallel near2 plate near2 capacitor) or (parallel-plate-capacitor)) and (heatsink or (heat near1 sink)) and (conductive) and (metal\$3 near3 (block or layer or region or film or medium))	USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/30 11:59
S47	33	((parallel near2 plate near2 capacitor) or (parallel-plate-capacitor)) and (heatsink or (heat near1 sink)) and (diode or laser)	US-PGPUB; USPAT	AND	ON	2006/01/30 11:42
S46	94	((parallel near2 plate near2 capacitor) or (parallel-plate-capacitor)) and (heatsink or (heat near1 sink))	US-PGPUB; USPAT	AND	ON	2006/01/30 11:42
S45	0	((parallel near2 plate near2 capacitor) or (parallel-plate-capacitor)) and "372"/\$.ccls. and (heatsink or (heat near1 sink))	USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/30 11:41
S44	1	((parallel near2 plate near2 capacitor) or (parallel-plate-capacitor)) and "372"/\$.ccls. and (heatsink or (heat near1 sink))	US-PGPUB; USPAT	AND	ON	2006/01/30 11:41
S42	29	((parallel near2 plate near2 capacitor) or (parallel-plate-capacitor)) and "372"/\$.ccls.	US-PGPUB; USPAT	AND	ON	2006/01/30 11:41
S43	0	((parallel near2 plate near2 capacitor) or (parallel-plate-capacitor)) and laser and (heatsink or (heat near1 sink))	USOCR; EPO; JPO; DERWENT	AND	ON	2006/01/30 11:31
S41	18	((parallel near2 plate near2 capacitor) or (parallel-plate-capacitor)) and laser and (heatsink or (heat near1 sink))	US-PGPUB; USPAT	AND	ON	2006/01/30 11:31
S40	650	((parallel near2 plate near2 capacitor) or (parallel-plate-capacitor)) and laser	US-PGPUB; USPAT	AND	ON	2006/01/30 09:59
S39	4227	((parallel near3 capacitor) or (parallel-plate-capacitor)) and laser	US-PGPUB; USPAT	AND	ON	2006/01/30 09:59
S38	711	((parallel near3 plate near3 capacitor) or (parallel-plate-capacitor)) and laser	US-PGPUB; USPAT	AND	ON	2006/01/30 09:59
S37	0	((parallel near3 plate near3 capacitor) or (parallel-plate-capacitor)) and laser	US-PGPUB; USPAT	AND	ON	2006/01/30 09:59
S36	0	(parallel near3 plate near3 capacitor) and laser	US-PGPUB; USPAT	AND	ON	2006/01/30 09:58
S35	1822	372/34,36,44.ccls.	US-PGPUB; USPAT	AND	ON	2006/01/27 14:20
S34	136	S31 not S30	US-PGPUB; USPAT	AND	ON	2006/01/27 14:20

S30	123	(laser) and (heatsink or (heat near2 sink)) and ((conductive or dielectric) near2 (layer or film or medium or region)) and (metal\$3 near2 (layer or film or medium or region)) and anode and cathode	USPAT	AND	ON	2006/01/27 13:59
S33	118	(laser) and (heatsink or (heat near2 sink)) and ((conductive or dielectric) near2 (layer or film or medium or region)) and (metal\$3 near1 (layer or film or medium or region or block or base or mount)) and anode and cathode	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/27 13:56
S31	136	(laser) and (heatsink or (heat near2 sink)) and ((conductive or dielectric) near2 (layer or film or medium or region)) and (metal\$3 near2 (layer or film or medium or region)) and anode and cathode	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/27 13:49
S29	1277	(laser) and (heatsink or (heat near2 sink)) and ((conductive or dielectric) near2 (layer or film or medium or region)) and (metal\$3 near2 (layer or film or medium or region))	USPAT	AND	ON	2006/01/27 13:44
S28	33	(laser) and (heatsink or (heat near2 sink)) and ((conductive or dielectric) near2 (layer or film or medium or region)) and (cathode and anode) and active and clad\$4 and substrate	USPAT	AND	ON	2006/01/27 13:43
S27	253	(laser) and (heatsink or (heat near2 sink)) and ((conductive or dielectric) near2 (layer or film or medium or region)) and ((cathode and anode) or electrode) and active and clad\$4 and substrate	USPAT	AND	ON	2006/01/27 13:37
S25	25	(laser near1 diode) and (heatsink or (heat near2 sink)) and (conductive near2 (layer or film or medium or region)) and (insulating near2 (layer or film or medium or region)) and active and clad\$4 and substrate	USPAT	AND	ON	2006/01/27 13:19
S26	1	(laser near1 diode) and (heatsink or (heat near2 sink)) and (conductive near2 (layer or film or medium or region)) and (insulating near2 (layer or film or medium or region)) and active and clad\$4 and substrate and capacitor	USPAT	AND	ON	2006/01/27 13:01
S24	93	(laser near1 diode) and (heatsink or (heat near2 sink)) and (conductive near2 (layer or film or medium or region)) and (insulating near2 (layer or film or medium or region))	USPAT	AND	ON	2006/01/27 13:00
S23	12	372/36.ccls. and (laser near1 diode) and (heatsink or (heat near2 sink)) and (conductive near2 (layer or film or medium or region)) and (insulating near2 (layer or film or medium or region))	USPAT	AND	ON	2006/01/27 12:55
S22	31	372/36.ccls. and (laser near1 diode) and capacitor	USPAT	AND	ON	2006/01/27 12:53
S21	391	372/36.ccls. and (laser near1 diode)	USPAT	AND	ON	2006/01/27 12:51
S20	645	372/36.ccls.	USPAT	AND	ON	2006/01/27 12:50
S6	921	372/36.ccls.	US-PGPUB; USPAT	AND	ON	2006/01/27 12:50
S19	3	("20020029875" "5661902" "6546030").PN. OR ("6917638").URPN.	US-PGPUB; USPAT; USOCR	AND	ON	2006/01/27 12:49
S18	70	(heatsink or (heat near2 sink)) and (conductive near2 (layer or region or medium or device)) and (laser near2 diode) and (electrode or (anode and cathode)) and "372"/\$.ccls.	US-PGPUB; USPAT	AND	ON	2006/01/27 12:46
S17	292	(heatsink or (heat near2 sink)) and (conductive near2 (layer or region or medium or device)) and (laser near2 diode) and (electrode or (anode and cathode))	US-PGPUB; USPAT	AND	ON	2006/01/27 12:46
S16	42	(metallic or block\$3) and ((heat near2 sink) or heatsink) and laser and capacitor and (packag\$3 or housing) and anode and cathode and "257"/\$.ccls.	US-PGPUB; USPAT	AND	ON	2006/01/27 12:08
S15	49	(metallic or block\$3) and ((heat near2 sink) or heatsink) and laser and capacitor and (packag\$3 or housing) and anode and cathode and "372"/\$.ccls.	US-PGPUB; USPAT	AND	ON	2006/01/27 12:08
S14	200	(metallic or block\$3) and ((heat near2 sink) or heatsink) and laser and capacitor and (packag\$3 or housing) and anode and cathode	US-PGPUB; USPAT	AND	ON	2006/01/27 12:08
S13	216233	(metallic or block\$3) and ((heat near2 sink) or heatsink) and laser and capacitor and (packag\$3 or housing) and anode or cathode	US-PGPUB; USPAT	AND	ON	2006/01/27 12:07

S12	1159	(metallic or block\$3) and ((heat near2 sink) or heatsink) and laser and capacitor and (packag\$3 or housing)	US-PGPUB; USPAT	AND	ON	2006/01/27 12:07
S11	1498	(metallic or block\$3) and ((heat near2 sink) or heatsink) and laser and capacitor	US-PGPUB; USPAT	AND	ON	2006/01/27 12:06
S10	143	S9 and (capacitor)	US-PGPUB; USPAT	AND	ON	2006/01/27 12:06
S8	57	S6 and (capacitor)	US-PGPUB; USPAT	AND	ON	2006/01/27 12:06
S3	5	(metallic near3 block\$3) and ((heat near2 sink) or heatsink) and laser and capacitor	US-PGPUB; USPAT	AND	ON	2006/01/27 12:06
S9	1822	372/36,34.ccls.	US-PGPUB; USPAT	AND	ON	2006/01/27 12:05
S7	1	S6 and (parallel near3 plate near3 capacitor)	US-PGPUB; USPAT	AND	ON	2006/01/27 11:44
S5	35	(Moto near2 Akihiro).in.	USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/27 11:41
S4	13	(Moto near2 Akihiro).in.	US-PGPUB; USPAT	AND	ON	2006/01/27 11:40
S1	1	"20040233946"	US-PGPUB; USPAT	AND	ON	2006/01/27 11:40
S2	1	("2001274500").PN.	JPO	OR	OFF	2006/01/27 11:33

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L24	0	((diode or semiconductor) near2 laser) and (conduct\$3 near2 (layer or film or region medium)) and (metal\$3 near2 (block or layer or film or region or medium)) and ((thermal\$3 or heat) near2 sink) and electrode and (capacitor with parallel)).clm.	US-PGPUB	AND	ON	2006/01/31 11:58
L25	1	((diode or semiconductor) near2 laser) and (conduct\$3 near2 (layer or film or region medium)) and (metal\$3 near2 (block or layer or film or region or medium)) and ((thermal\$3 or heat) near2 sink) and (electrode or (anode and cathode)) and (capacitor with parallel)).clm.	US-PGPUB	AND	ON	2006/01/31 11:58
L26	12	((diode or semiconductor) near2 laser) and (conduct\$3 near2 (layer or film or region medium)) and (metal\$3 near2 (block or layer or film or region or medium)) and ((thermal\$3 or heat) near2 sink) and (electrode or (anode and cathode)) and (capacitor with parallel))	US-PGPUB; USPAT	AND	ON	2006/01/31 11:59
L27	0	((diode or semiconductor) near2 laser) and (conduct\$3 near2 (layer or film or region medium)) and (metal\$3 near2 (block or layer or film or region or medium)) and ((thermal\$3 or heat) near2 sink) and (electrode or (anode and cathode)) and (capacitor with parallel))	USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/31 11:58
L28	0	26 not 14	US-PGPUB; USPAT	AND	ON	2006/01/31 11:59
L29	3141	(capacitor near2 plate near2 parallel)	US-PGPUB; USPAT	AND	ON	2006/01/31 12:00
L30	127	(capacitor near2 plate near2 parallel) and (laser near2 (semiconductor or diode))	US-PGPUB; USPAT	AND	ON	2006/01/31 12:00
L31	27	(capacitor near2 plate near2 parallel) and "372"/\$.ccls.	US-PGPUB; USPAT	AND	ON	2006/01/31 12:13
L32	8	(capacitor near2 plate near2 parallel) and (laser near2 (semiconductor or diode)) and ((heat or thermal\$3) near2 sink)	US-PGPUB; USPAT	AND	ON	2006/01/31 12:01
L33	2	(capacitor near2 plate near2 parallel) and (laser near2 (semiconductor or diode)) and ((heat or thermal\$3) near2 sink) and "372"/\$.ccls.	US-PGPUB; USPAT	AND	ON	2006/01/31 12:01
L34	2	(capacitor near2 plate near2 parallel) and "372"/\$.ccls. and ((heat or thermal\$3) near2 sink)	US-PGPUB; USPAT	AND	ON	2006/01/31 12:13



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#1	((parallel plate capacitor) and laser and (heat sink))<in>metadata)	0
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#2	((parallel capacitor) and laser and (heat sink))<in>metadata)	0
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